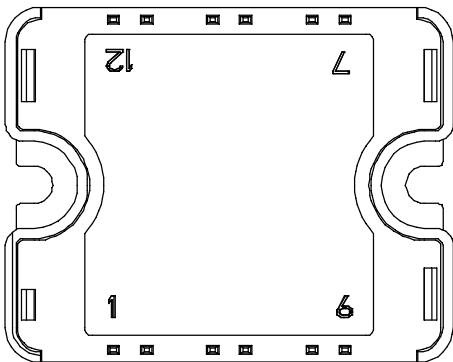
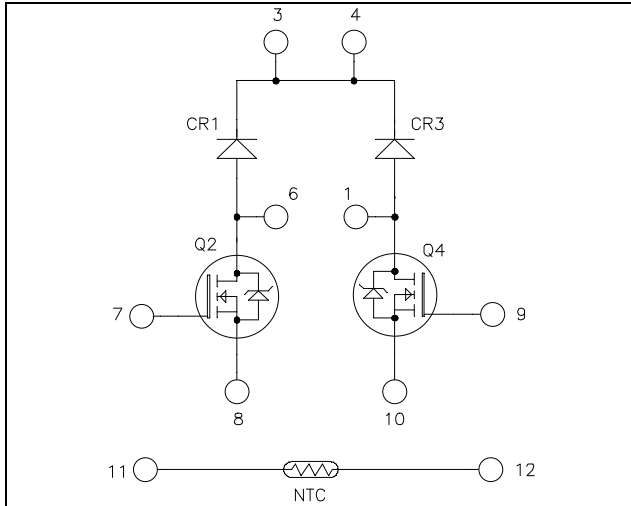


**Dual boost chopper  
Super Junction MOSFET  
SiC chopper diode**

**$V_{DSS} = 900V$**   
 **$R_{DSon} = 120m\Omega \text{ max @ } T_j = 25^\circ C$**   
 **$I_D = 30A \text{ @ } T_c = 25^\circ C$**



Pins 3/4 must be shorted together

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	900	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	30
		$T_c = 80^\circ C$	23
$I_{DM}$	Pulsed Drain current	75	
$V_{GS}$	Gate - Source Voltage	$\pm 20$	V
$R_{DSon}$	Drain - Source ON Resistance	120	$m\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	250
$I_{AR}$	Avalanche current (repetitive and non repetitive)	8.8	A
$E_{AR}$	Repetitive Avalanche Energy	2.9	mJ
$E_{AS}$	Single Pulse Avalanche Energy	1940	

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

### Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

### Features

- **COOLMOS**  
Power Semiconductors
  - Ultra low  $R_{DSon}$
  - Low Miller capacitance
  - Ultra low gate charge
  - Avalanche energy rated
  - Very rugged
- **SiC Schottky Diode**
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature Independent switching behavior
  - Positive temperature coefficient on VF
- Very low stray inductance
  - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 900V$   $T_j = 25^\circ\text{C}$			100	$\mu\text{A}$
		$V_{GS} = 0V, V_{DS} = 900V$   $T_j = 125^\circ\text{C}$		500		
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 26A$		100	120	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 3\text{mA}$	2.5	3	3.5	V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			100	$\text{nA}$

**Dynamic Characteristics**

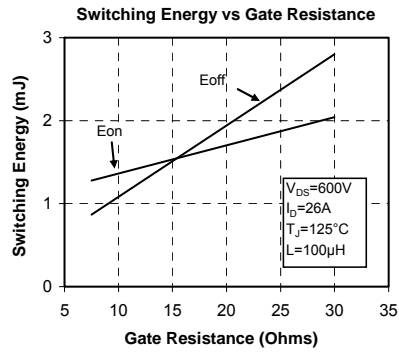
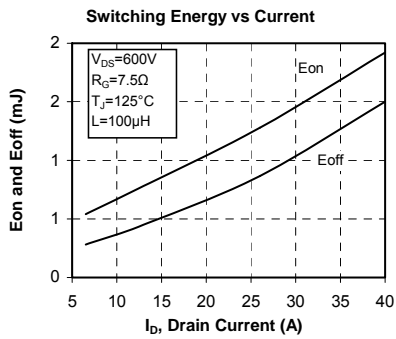
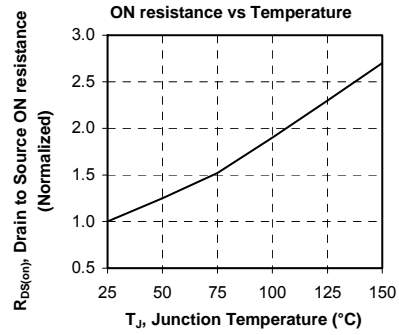
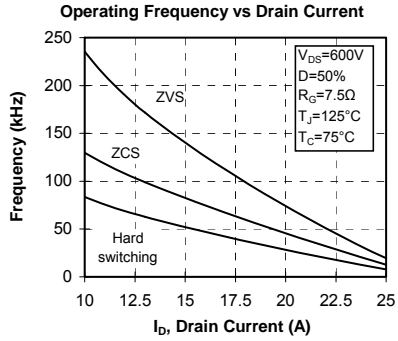
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0V ; V_{DS} = 100V$ $f = 1\text{MHz}$		6800		$\text{pF}$
$C_{oss}$	Output Capacitance			330		
$Q_g$	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 400V$ $I_D = 26A$		270		$\text{nC}$
$Q_{gs}$	Gate – Source Charge			32		
$Q_{gd}$	Gate – Drain Charge			115		
$T_{d(on)}$	Turn-on Delay Time	<b>Inductive Switching (<math>125^\circ\text{C}</math>)</b> $V_{GS} = 10V$ $V_{Bus} = 600V$ $I_D = 26A$ $R_G = 7.5\Omega$		70		$\text{ns}$
$T_r$	Rise Time			20		
$T_{d(off)}$	Turn-off Delay Time			400		
$T_f$	Fall Time			25		
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ <math>25^\circ\text{C}</math></b> $V_{GS} = 10V ; V_{Bus} = 600V$ $I_D = 26A ; R_G = 7.5\Omega$		900		$\mu\text{J}$
$E_{off}$	Turn-off Switching Energy			750		
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ <math>125^\circ\text{C}</math></b> $V_{GS} = 10V ; V_{Bus} = 600V$ $I_D = 26A ; R_G = 7.5\Omega$		1278		$\mu\text{J}$
$E_{off}$	Turn-off Switching Energy			867		

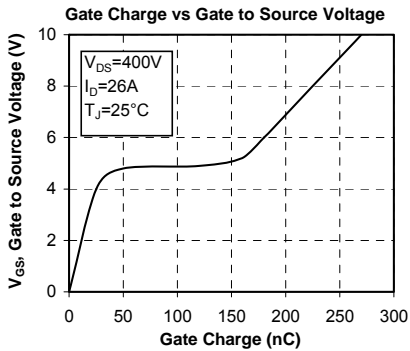
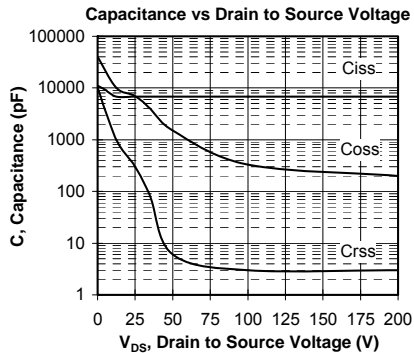
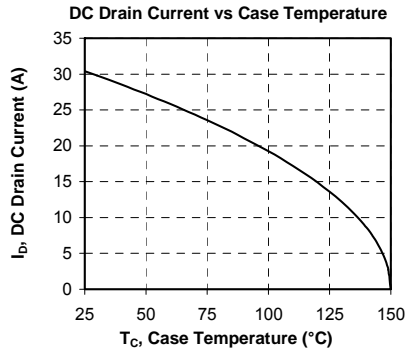
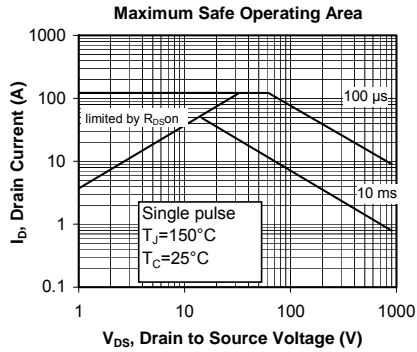
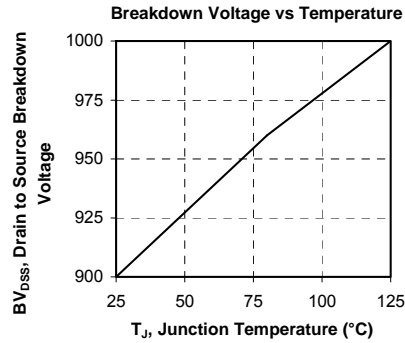
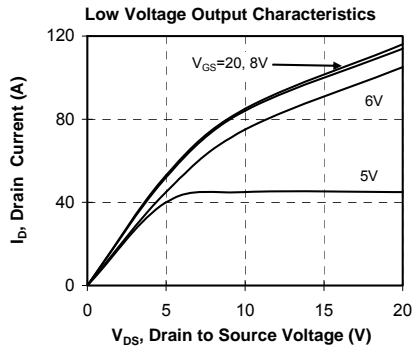
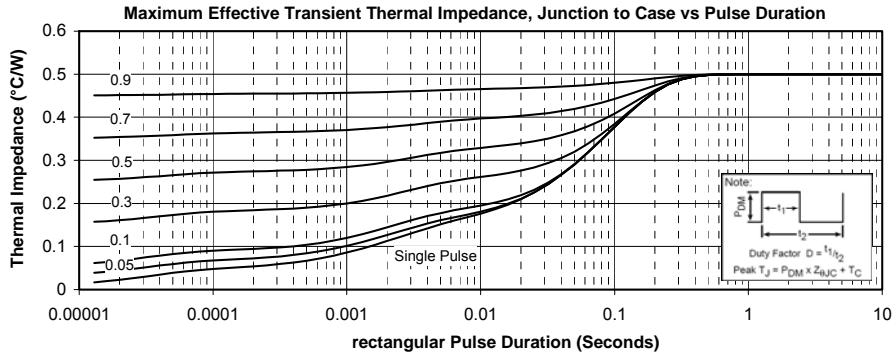
**SiC chopper diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		1200			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 1200V$	$T_j = 25^\circ\text{C}$	32	200	$\mu\text{A}$
			$T_j = 175^\circ\text{C}$	56	1000	
$I_F$	DC Forward Current	$T_c = 100^\circ\text{C}$		10		A
$V_F$	Diode Forward Voltage	$I_F = 10A$	$T_j = 25^\circ\text{C}$	1.6	1.8	V
			$T_j = 175^\circ\text{C}$	2.3	3	
$Q_C$	Total Capacitive Charge	$I_F = 10A, V_R = 600V$ $di/dt = 500A/\mu\text{s}$		40		$\text{nC}$
C	Total Capacitance	$f = 1\text{MHz}, V_R = 200V$		96		$\text{pF}$
		$f = 1\text{MHz}, V_R = 400V$		69		

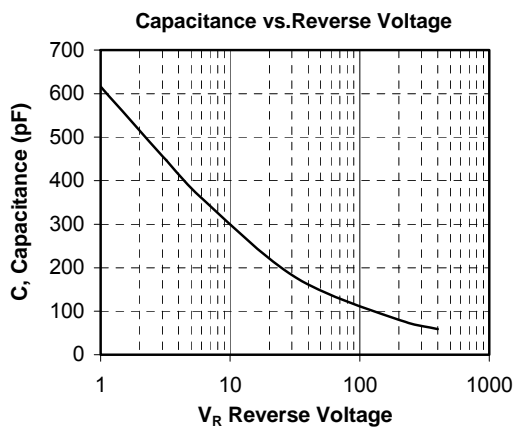
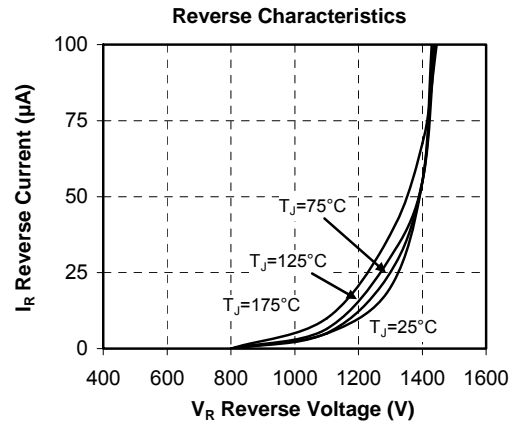
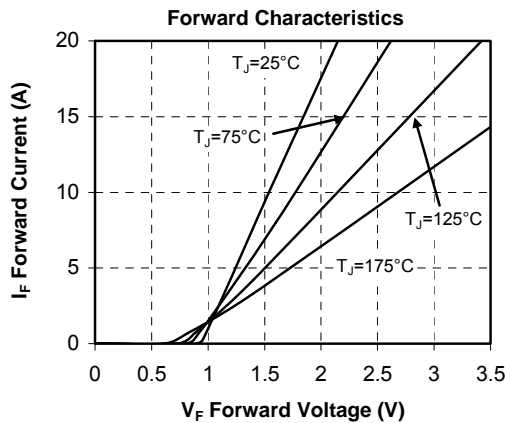
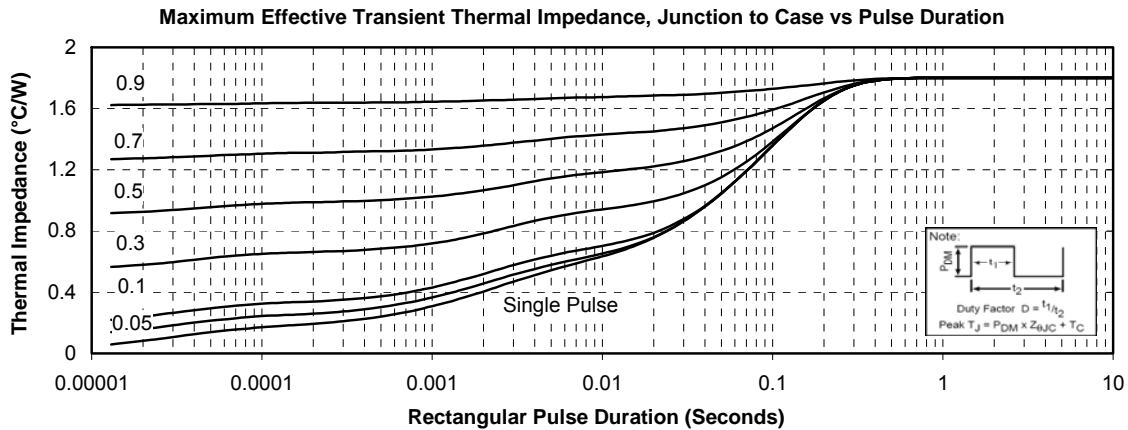


## Typical CoolMOS Performance Curve





## Typical SiC Diode Performance Curve



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